

SNS COLLEGE OF ENGINEERING



Coimbatore-35 An Autonomous Institution

Accredited by NBA – AICTE and Accredited by NAAC – UGC with 'A+' Grade Approved by AICTE, New Delhi & Affiliated to Anna University, Chennai

DEPARTMENT OF ELECTRONICS & COMMUNICATION ENGINEERING

19EC505-VLSI DESIGN

III YEAR/ V SEMESTER

UNIT 2 -COMBINATIONAL LOGIC CIRCUITS







- ➤ A Brief History
- > CMOS Gate Design
- ➤ Pass Transistors
- ➤ Transmission Gate logic
- > Activity
- **>** Assessment
- > Summary







1958: First integrated circuit

> Flip-flop using two transistors

➤ Built by Jack Kilby at Texas Instruments

2003-Intel Pentium 4 mprocessor (55 million transistors)

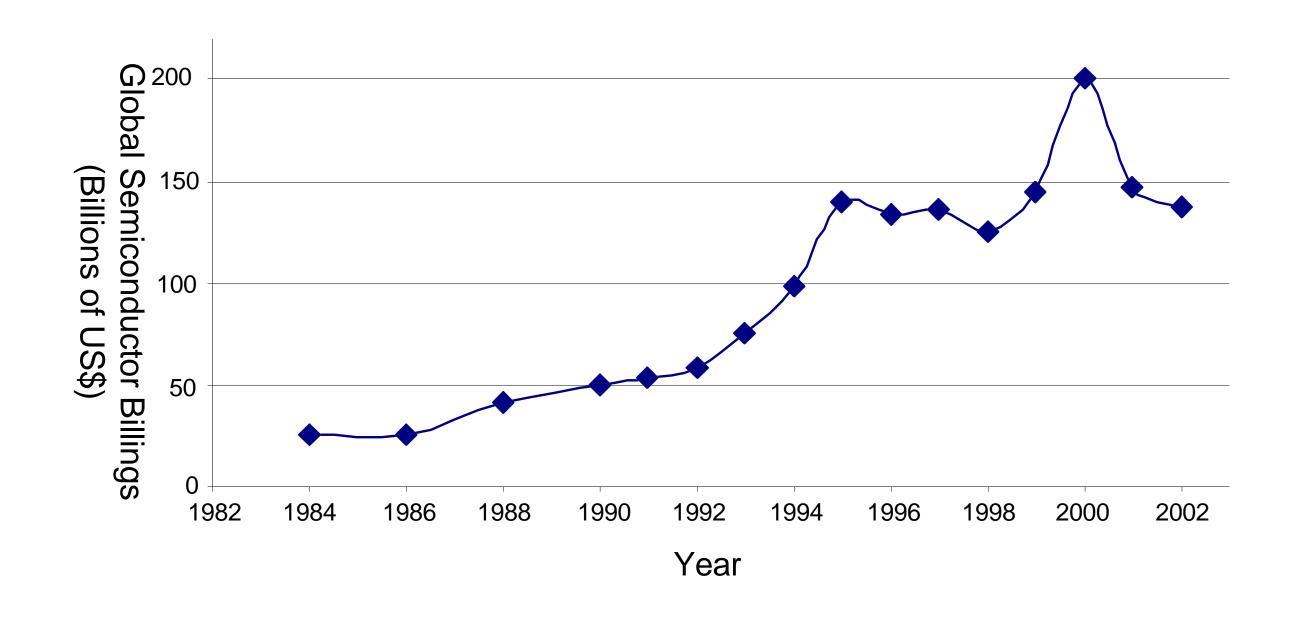
512 Mbit DRAM (> 0.5 billion transistors) miniaturization of transistors Smaller is cheaper,

faster, stant ower power! Revolutionary effects on society





Annual Sales









> Bipolar transistors

- npn or pnp silicon structure
- Small current into very thin base layer controls large currents between emitter and collector
- Base currents limit integration density

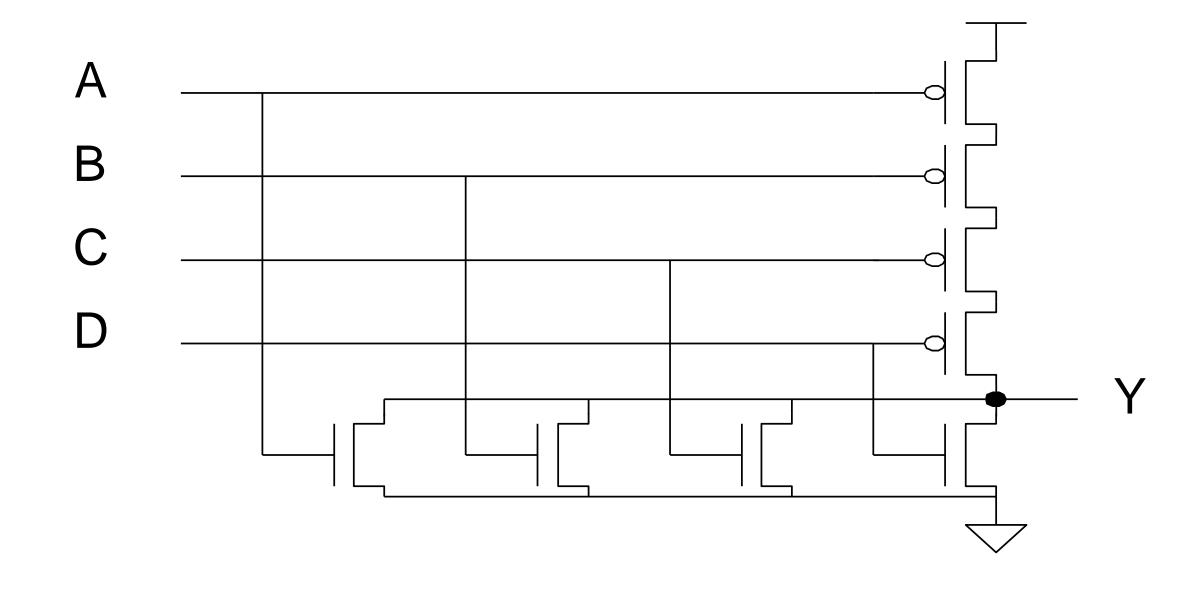
➤ Metal Oxide Semiconductor Field Effect Transistors

- nMOS and pMOS MOSFETS
- Voltage applied to insulated gate controls current between source and drain
- Low power allows very high integration





CMOS Gate Design-4 input NOR

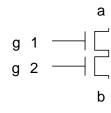






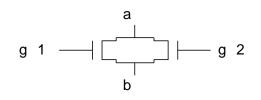
Series and Parallel Connections

- nMOS: 1 = ON
- pMOS: 0 = ON
- Series: both must be ON
- Parallel: either can be ON

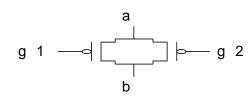


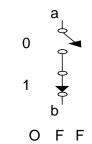
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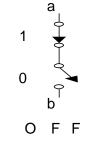
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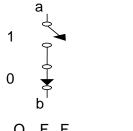


(c)











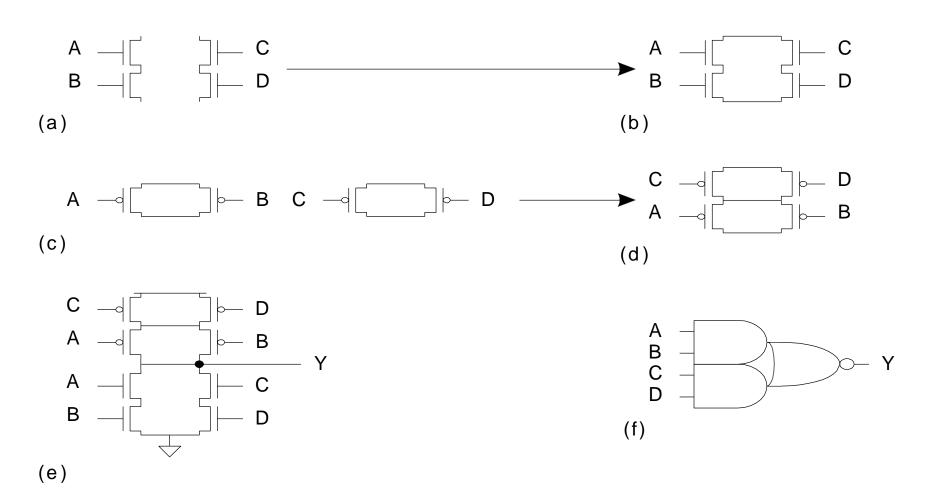
- Complementary CMOS gates always produce 0 or 1
- Ex: NAND gate- .ns—n-MOS Series—pMOS parallel
 - Series nMOS: Y=0 when both inputs are 1
 - Thus Y=1 when either input is 0
 - Requires parallel pMOS
- Rule of Conduction Complements
 - Pull-up network is complement of pull-down
 - Parallel -> series, series -> parallel





Compound Gates

- Compound gates can do any inverting function
- Ex: $Y = \overline{A B + C D}$ (AND-AND-OR-INVERT, AOI22)

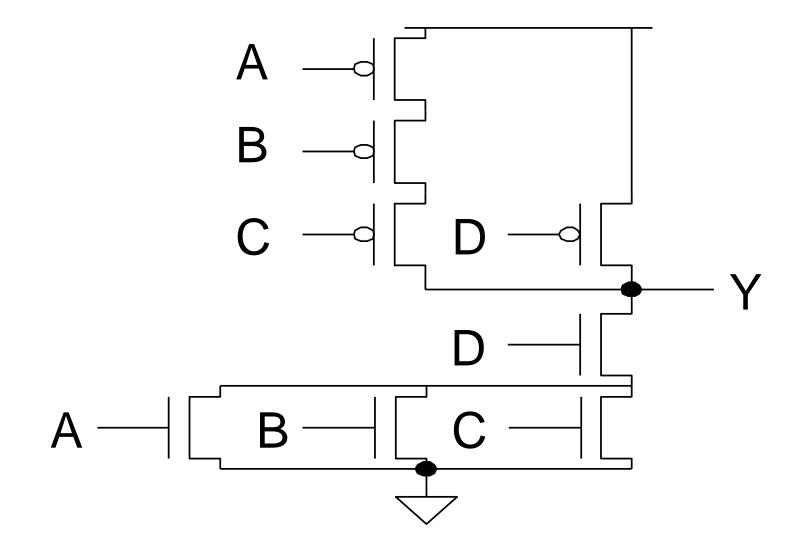








$$Y = \overline{(A+B+C)D}$$





Strength of Signal



How close it approximates ideal voltage source

V_{DD} and GND rails are strongest 1 and 0

g ⊥ s⊡d

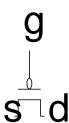
•nMOS pass strong 0

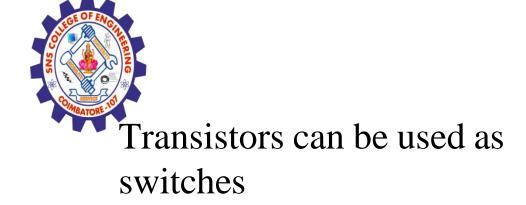
But degraded or weak 1

•pMOS pass strong 1

But degraded or weak 0

Thus nMOS are best for pull-down network







Pass Transistors

$$g = 0$$

$$s - - d$$

Input
$$g = 1$$
 Output $0 \rightarrow strong 0$

$$g = 1$$

 $s \rightarrow d$

$$g = 1$$

1————degraded 1

$$g = 0$$

 $s \rightarrow 0$

Input
$$g = 0$$

Output

 $0 \rightarrow c$

degraded 0

 $g = 0$
 $g = 0$
 c

strong 1

$$g=1$$
 $s \rightarrow d$





Transmission Gates

- Pass transistors produce degraded outputs
- Transmission gates pass both 0 and 1 well

$$g = 0$$
, $gb = 1$
 $a - b$

$$g = 1$$
, $gb = 0$
 $a \rightarrow b$

$$g = 1$$
, $gb = 0$
 $0 \longrightarrow \infty$ strong 0

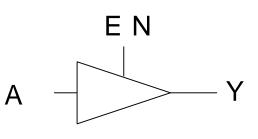
$$g = 1$$
, $gb = 0$
 $1 \rightarrow \infty$ strong 1





• Tristate buffer produces Z when not enabled

	EN	А	Υ
	0	0	Z
	0	1	Z
	1	0	0
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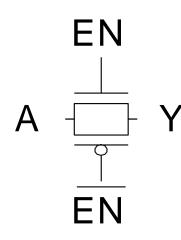






Non restoring Tristate

- Transmission gate acts as tristate buffer
 - Only two transistors
 - But non restoring
 - Noise on A is passed on to Y

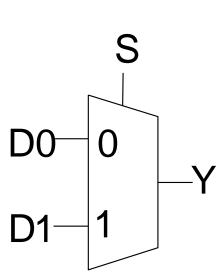






S	D1	D0	Υ
0	X	0	0
0	X	1	1
1	0	X	0
1 ant	1	X	1

DESIGN/T.G.Ramabharathi/ AssisProfessor/ECE/SNSCE



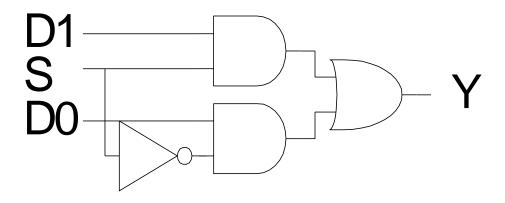


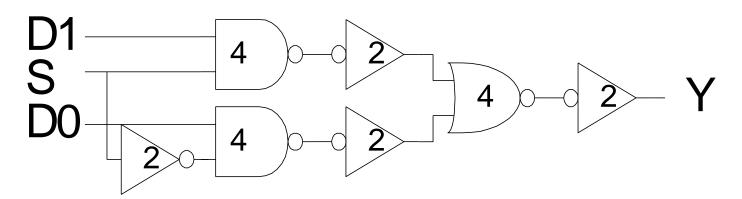
Gate-Level Mux Design



 $Y = SD_1 + \overline{S}D_0$ (too many transistors)

How many transistors are needed? 20



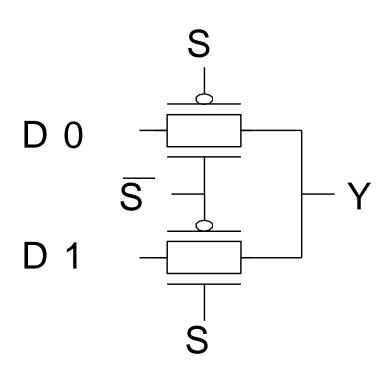








- Nonrestoring mux uses two transmission gates
 - Only 4 transistors





Assessment



How many transistors are needed to

make 2:1 Mux? ---

Draw 2:1 mux using TG

Draw 4:1 mux using TG

nMOS pass strong -----

But degraded or weak -----

pMOS pass strong -----

But degraded or weak -----

Thus nMOS are best for pull-down network



THANK YOU